

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE 5-1002

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PATENT & TRADEMARK OFFICE
Application Serial No. 09/943,180
Filing Date August 29, 2001
Inventor John T. Moore et al.
Assignee Micron Technology, Inc.
Group Art Unit Unknown
Examiner Unknown
Attorney's Docket No. MI22-1776
Title: Capacitors, Methods of Forming Capacitors, and Methods of Forming
Capacitor Dielectric Layers

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PRELIMINARY AMENDMENT

To: Box Non-Fee Amendment
Assistant Commissioner for Patents
Washington, D.C. 20231

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Please enter the following amendment prior to examining the above-identified application.

AMENDMENTS

In the Specification

Please replace the second paragraph under the heading "Detailed Description of the Preferred Embodiments", beginning at line 5 on page 7, with the following clean replacement paragraph in accordance with 37 CFR § 1.121(b)(1)(ii). A marked-up version showing amendments to the specification paragraph being changed is provided in one or more

accompanying pages separate from this amendment in accordance with 37 CFR § 1.121(b)(1)(iii).

A wafer fragment in process in accordance with a method of forming a capacitor in accordance with an aspect of the invention is indicated generally with reference numeral 10. Such comprises a bulk monocrystalline silicon substrate 12. In the context of this document, the term "semiconductor substrate" or "semiconductive substrate" is defined to mean any construction comprising semiconductive material, including, but not limited to, bulk semiconductive materials such as a semiconductive wafer (either alone or in assemblies comprising other materials thereon), and semiconductive material layers (either alone or in assemblies comprising other materials). The term "substrate" refers to any supporting structure, including, but not limited to, the semiconductive substrates described above. An insulative layer 14, for example doped or undoped silicon dioxide, or silicon nitride, is formed over bulk substrate 12.

In the Claims

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 CFR § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked-up version showing the amendment to claim 8 is provided in one or more accompanying pages separate from this amendment in accordance with 37 CFR § 1.121(c)(1)(ii). No claim other than claim 8 has been changed relative to the immediate prior version, and there are no added or canceled claims.